

RoHS

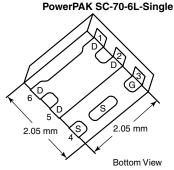
COMPLIANT

HALOGEN FREE

### **Vishay Siliconix**

# N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) Max.	Max. I <sub>D</sub> (A) <sup>a</sup> Q <sub>g</sub> (Ty			
100	0.083 at V <sub>GS</sub> = 10 V	11.3	3.5 nC		
	0.130 at V <sub>GS</sub> = 4.5 V	9	3.5110		



Ordering Information:

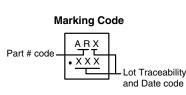
SiA416DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

#### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- 100  $\%~\text{R}_{g}$  and UIS Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

#### **APPLICATIONS**

- DC/DC Converters
- Full-Bridge Converters
- For Power Bricks and POL Power





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	<b>S</b> (T <sub>A</sub> = 25 °C, unle	ess otherwise not	ed)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	100	V		
Gate-Source Voltage		V <sub>GS</sub>	± 20	v	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C		11.3		
	T <sub>C</sub> = 70 °C		9		
	T <sub>A</sub> = 25 °C	I <sub>D</sub>	4.8 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		3.9 <sup>b, c</sup>		
Pulsed Drain Current (t = 300 μs)		I <sub>DM</sub>	15	A	
Cantinuaus Courses Drain Diada Current	T <sub>C</sub> = 25 °C		12		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	2.9 <sup>b, c</sup>		
Single Pulse Avalanche Current		I <sub>AS</sub>	3		
Single Pulse Avalanche Energy	Pulse Avalanche Energy L = 0.1 mH		0.45	mJ	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C		19		
	T <sub>C</sub> = 70 °C		12		
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.5 <sup>b, c</sup>	W	
	T <sub>A</sub> = 70 °C		2.2 <sup>b, c</sup>		
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	**		
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, f</sup>	$t \le 5 s$	R <sub>thJA</sub>	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	5.3	6.5		

Notes:

a. Based on T<sub>C</sub> = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 80 °C/W.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static					•		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$	100			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = 250 μA		54		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250 \ \mu A$		- 4.4			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.6		3	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55 ^{\circ}\text{C}$			1 10	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	10		-	A	
	D(01)	$V_{GS} = 10 \text{ V}, I_D = 3.2 \text{ A}$		0.068	0.083		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 2.6 \text{ A}$		0.092	0.130	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{\rm DS} = 10 \text{ V}, \text{ I}_{\rm D} = 3.2 \text{ A}$		8		S	
Dynamic <sup>b</sup>	513			1 -	l	-	
Input Capacitance	C <sub>iss</sub>			295		[	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V, f = 1 MHz		92		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			16			
		V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.8 A		6.5	10		
Total Gate Charge	Qg			3.5	5.3		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 4.8 \text{ A}$		1.2		nC	
Gate-Drain Charge	Q <sub>gd</sub>	20 00 2		1.9			
Output Charge	Q <sub>oss</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}$		7.6			
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.4	1.8	3.6	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			5	10		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 50 V, $R_L$ = 12.8 $\Omega$		13	25	-	
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong$ 3.9 A, $\text{V}_\text{GEN}$ = 10 V, $\text{R}_\text{g}$ = 1 $\Omega$		10	20		
Fall Time	t <sub>f</sub>			10	20		
Turn-On Delay Time	t <sub>d(on)</sub>			25	50	ns	
Rise Time	t <sub>r</sub>	$V_{DD}$ = 50 V, $R_L$ = 12.8 $\Omega$		100	200	-	
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong$ 3.9 A, $\text{V}_\text{GEN}$ = 4.5 V, $\text{R}_\text{g}$ = 1 $\Omega$		15	30		
Fall Time	t <sub>f</sub>			25	50		
Drain-Source Body Diode Characteristic	cs					<b>I</b>	
Continuous Source-Drain Diode Current	ا <sub>S</sub>	$T_{C} = 25 \ ^{\circ}C$			12	•	
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				15	A	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 3.9 A		0.85	1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			30	60	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	L = 2.0.4 dl/dt = 100.4/vs T = 05.00		30	60	nC	
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F = 3.9 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, \text{ T}_J = 25 ^\circ\text{C}$		20			
Reverse Recovery Rise Time	t <sub>b</sub>	-		10		ns	

Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

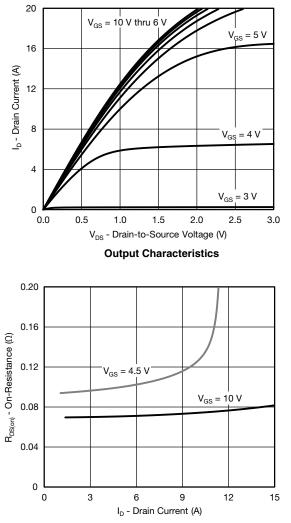
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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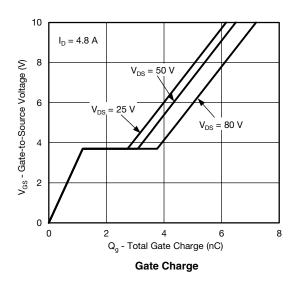


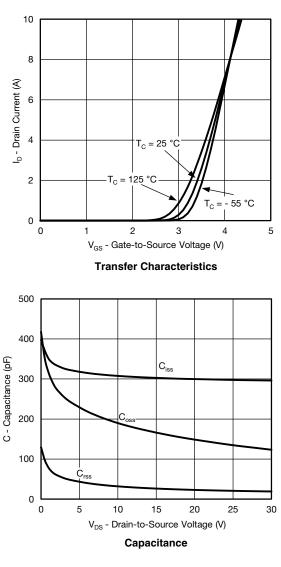
### SiA416DJ Vishay Siliconix

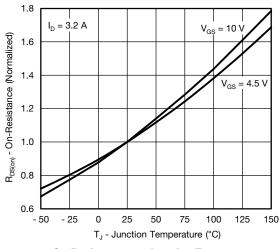
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



**On-Resistance vs. Drain Current and Gate Voltage** 







**On-Resistance vs. Junction Temperature** 

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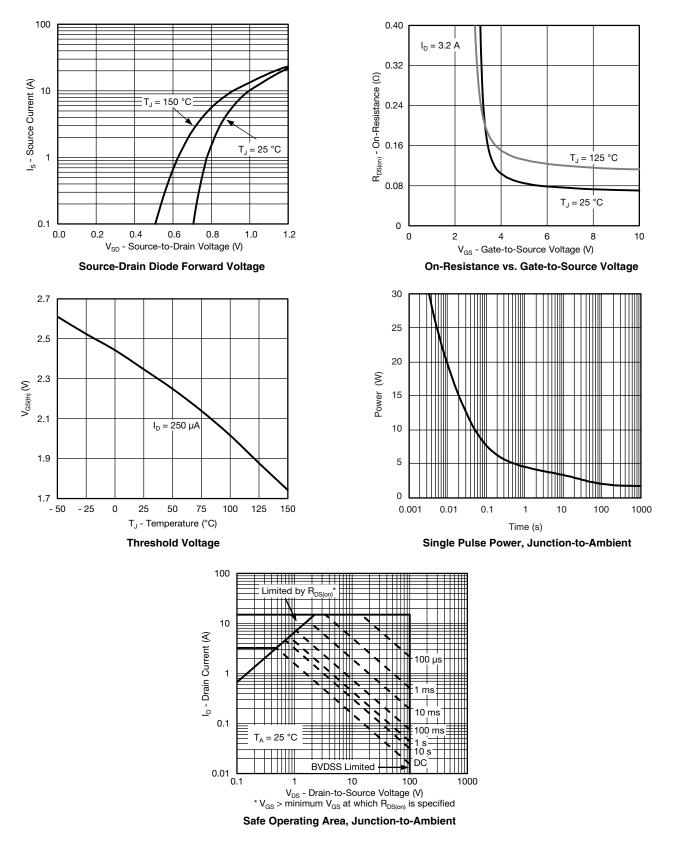
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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

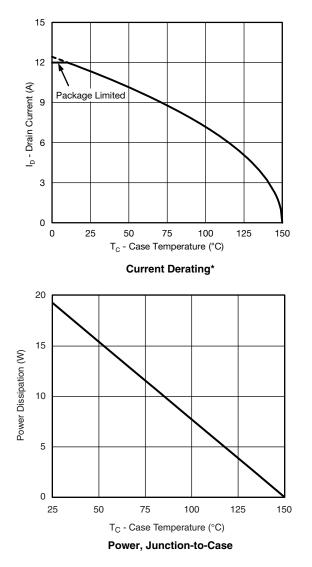


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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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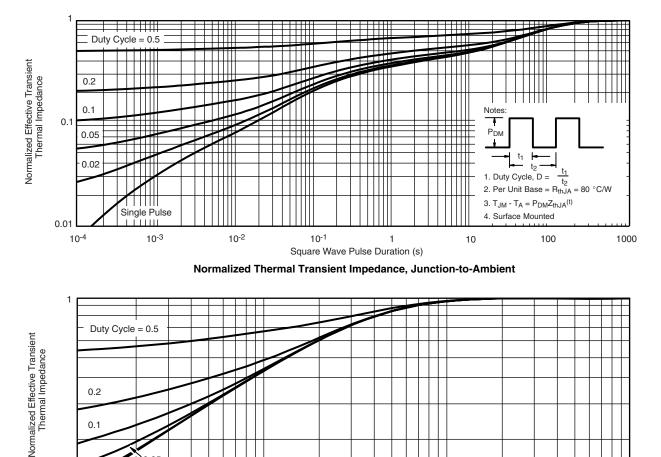


#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

0.05

0.02 Single Pulse

0.1



10<sup>-3</sup>

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?63649</u>.

Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Case

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10<sup>-1</sup>



# PowerPAK<sup>®</sup> SC70-6L

VISHA

# b PIN2 PIN1 PIN3 \_ ₹



b

PIN3

\_\_ ₿

PIN2

PIN1

¥

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<sup>1</sup> 



#### RECOMMENDED PAD LAYOUT FOR PowerPAK<sup>®</sup> SC70-6L Single



Dimensions in mm/(Inches)

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